



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



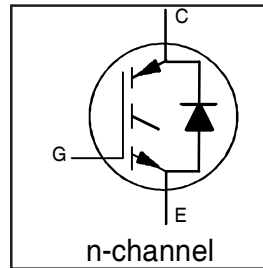
IRG4BC30UDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFast SOFT RECOVERY DIODE

UltraFast CoPack IGBT

Features

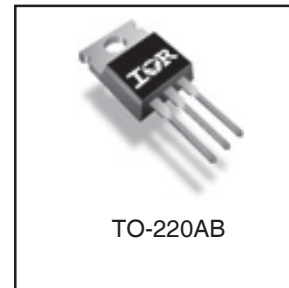
- UltraFast: Optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.95V$
@ $V_{GE} = 15V, I_C = 12A$

Benefits

- Generation -4 IGBT's offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs . Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	23	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	12	
I_{CM}	Pulsed Collector Current ①	92	
I_{LM}	Clamped Inductive Load Current ②	92	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current	92	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	°C
T_{STG}			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	1.2	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.50	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	80	
Wt	Weight	-----	2 (0.07)	-----	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	----	----	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	----	0.63	----	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	----	1.95	2.1	V	I _C = 12A
		----	2.52	----		I _C = 23A
		----	2.09	----		I _C = 12A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	----	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	----	-11	----	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	3.1	8.6	----	S	V _{CE} = 100V, I _C = 12A
I _{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	V _{GE} = 0V, V _{CE} = 600V
		----	----	2500		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	----	1.4	1.7	V	I _C = 12A
		----	1.3	1.6		I _C = 12A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q _g	Total Gate Charge (turn-on)	----	50	75		I _C = 12A	
Q _{ge}	Gate - Emitter Charge (turn-on)	----	8.1	12	nC	V _{CC} = 400V	
Q _{gc}	Gate - Collector Charge (turn-on)	----	18	27		V _{GE} = 15V	
t _{d(on)}	Turn-On Delay Time	----	40	----		T _J = 25°C	
t _r	Rise Time	----	21	----	ns	I _C = 12A, V _{CC} = 480V	
t _{d(off)}	Turn-Off Delay Time	----	91	140		V _{GE} = 15V, R _G = 23Ω	
t _f	Fall Time	----	80	130		Energy losses include "tail" and diode reverse recovery.	
E _{on}	Turn-On Switching Loss	----	0.38	----		mJ	See Fig. 9, 10, 11, 18
E _{off}	Turn-Off Switching Loss	----	0.16	----			
E _{ts}	Total Switching Loss	----	0.54	0.9		mJ	T _J = 150°C, See Fig. 9, 10, 11, 18
t _{d(on)}	Turn-On Delay Time	----	40	----			
t _r	Rise Time	----	22	----		ns	I _C = 12A, V _{CC} = 480V
t _{d(off)}	Turn-Off Delay Time	----	120	----			V _{GE} = 15V, R _G = 23Ω
t _f	Fall Time	----	180	----			Energy losses include "tail" and diode reverse recovery.
E _{ts}	Total Switching Loss	----	0.89	----	Measured 5mm from package		
L _E	Internal Emitter Inductance	----	7.5	----	nH		
C _{ies}	Input Capacitance	----	1100	----	pF	V _{GE} = 0V	
C _{oes}	Output Capacitance	----	73	----		V _{CC} = 30V	
C _{res}	Reverse Transfer Capacitance	----	14	----		f = 1.0MHz	
t _{rr}	Diode Reverse Recovery Time	----	42	60	ns	T _J = 25°C See Fig.	
I _{rr}	Diode Peak Reverse Recovery Current	----	80	120		T _J = 125°C 14	
Q _{rr}	Diode Reverse Recovery Charge	----	3.5	6.0	A	T _J = 25°C See Fig.	
		----	5.6	10		T _J = 125°C 15	
di _(rec) /dt	Diode Peak Rate of Fall of Recovery During t _b	----	80	180	nC	T _J = 25°C See Fig.	
		----	220	600		T _J = 125°C 16	
		----	180	----	A/μs	T _J = 25°C See Fig.	
		----	120	----		T _J = 125°C 17	

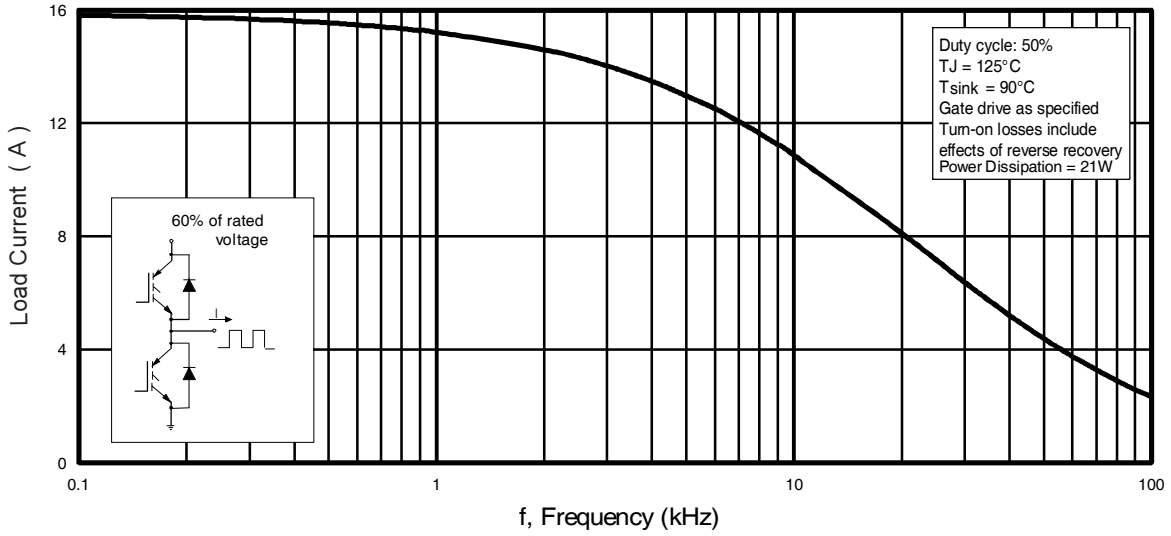


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

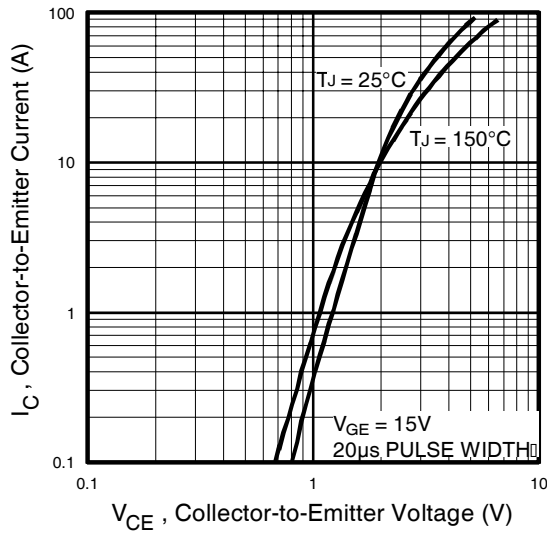


Fig. 2 - Typical Output Characteristics

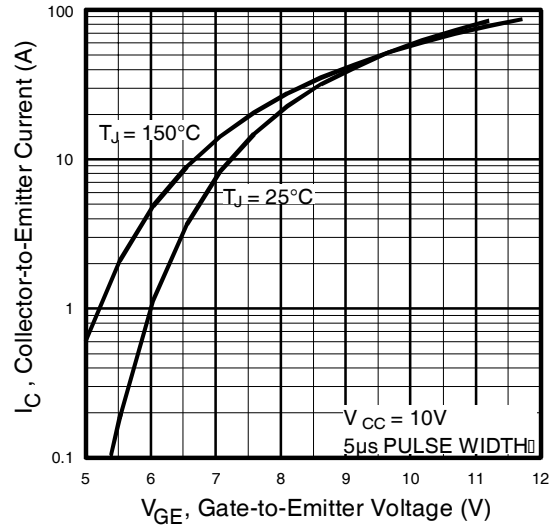


Fig. 3 - Typical Transfer Characteristics

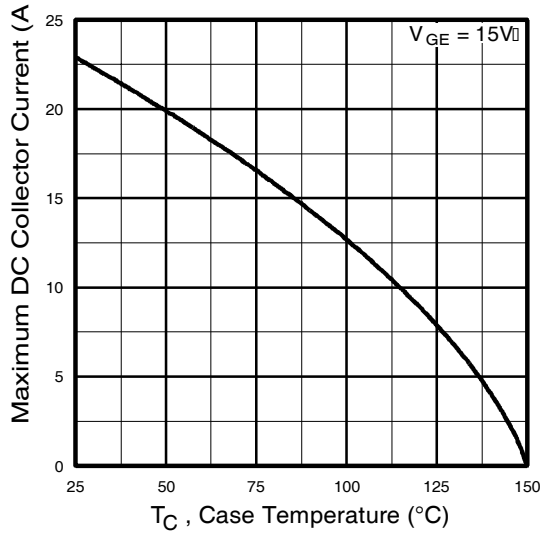


Fig. 4 - Maximum Collector Current vs. Case Temperature

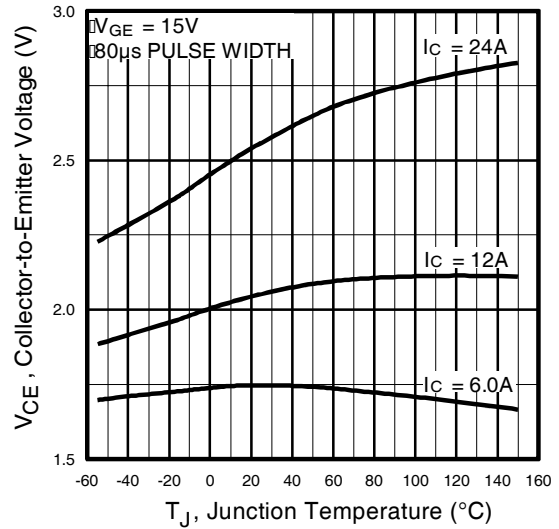


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

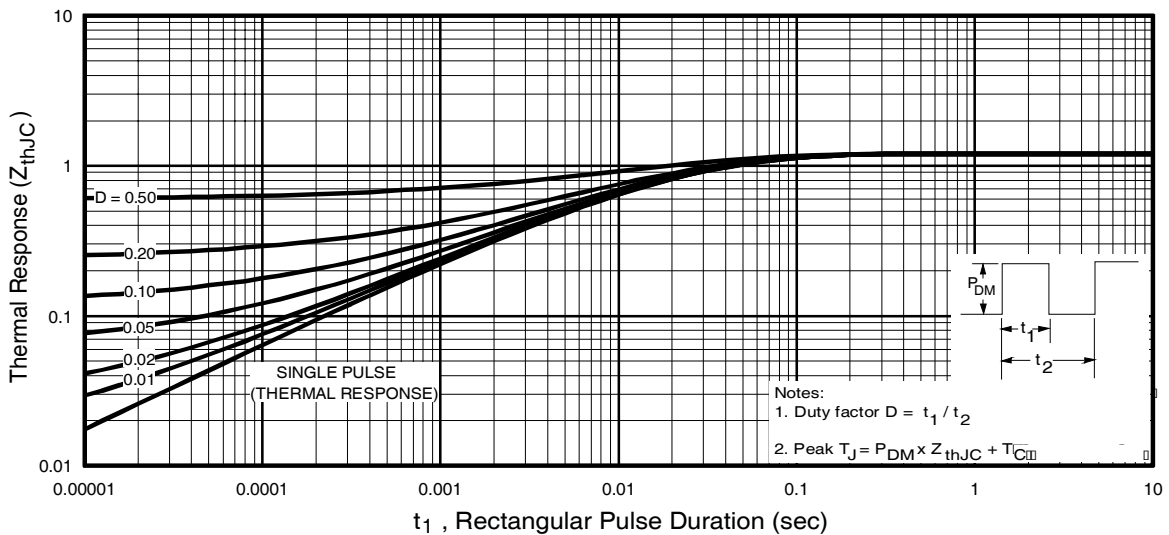


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

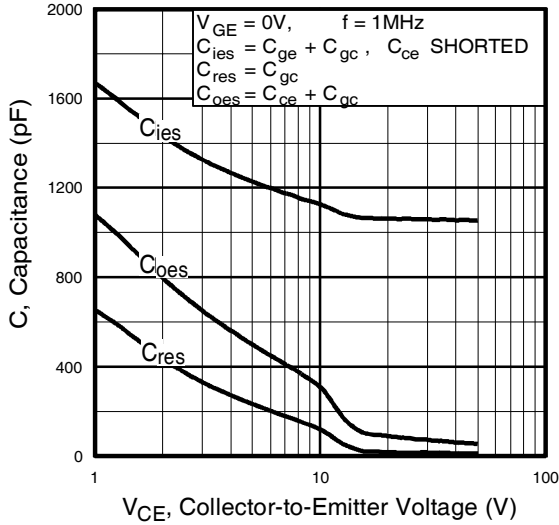


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

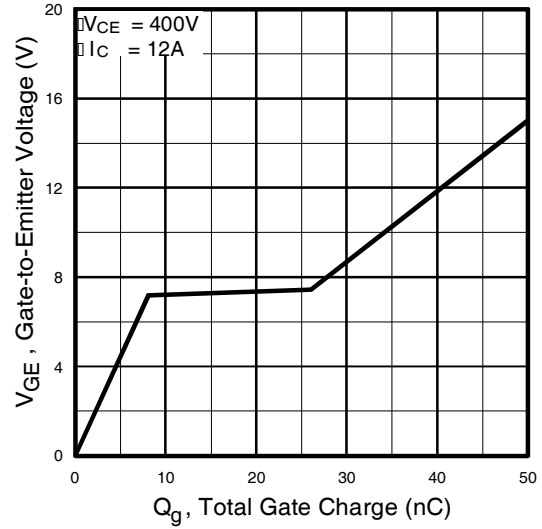


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

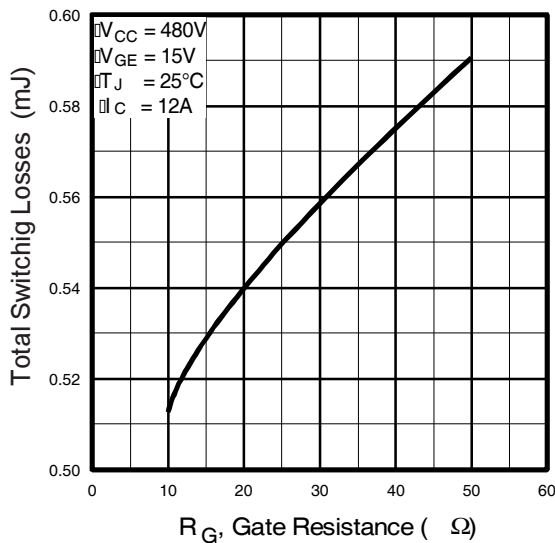


Fig. 9 - Typical Switching Losses vs. Gate Resistance

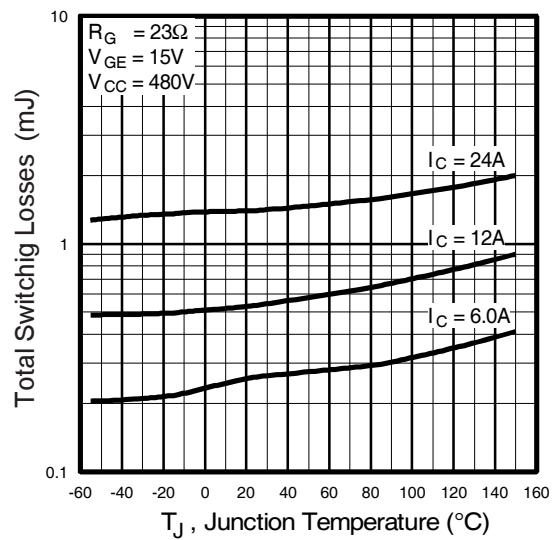


Fig. 10 - Typical Switching Losses vs. Junction Temperature

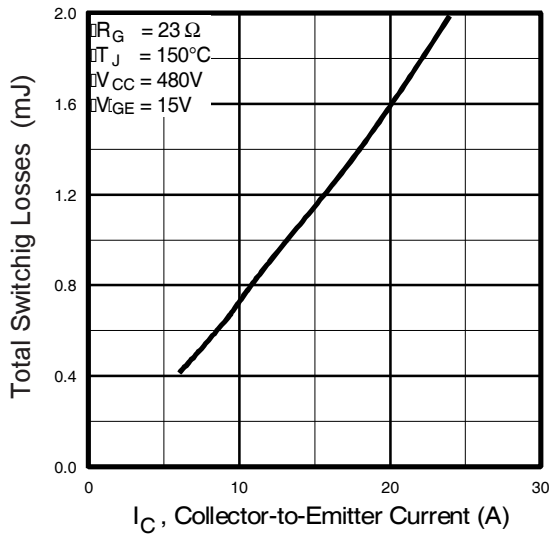


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

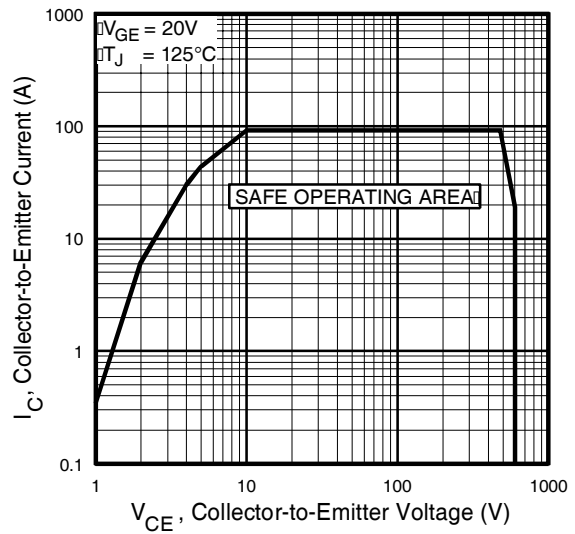


Fig. 12 - Turn-Off SOA

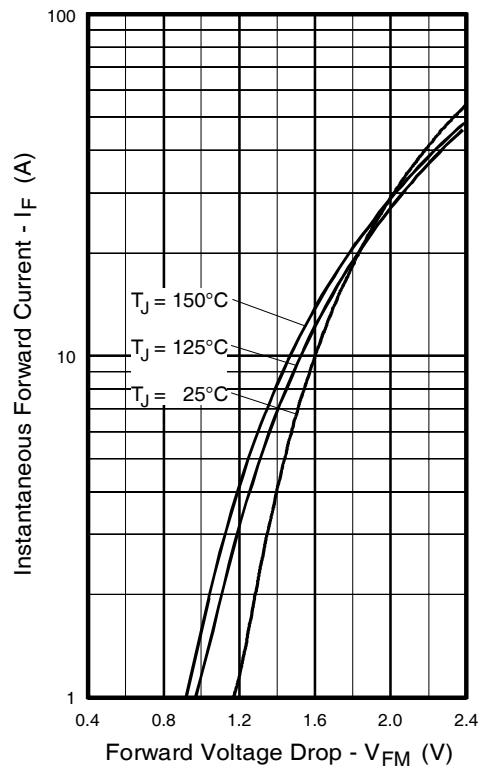


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

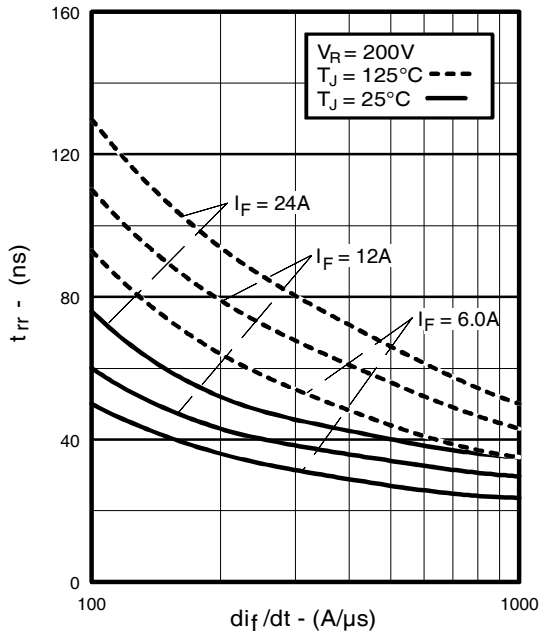


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

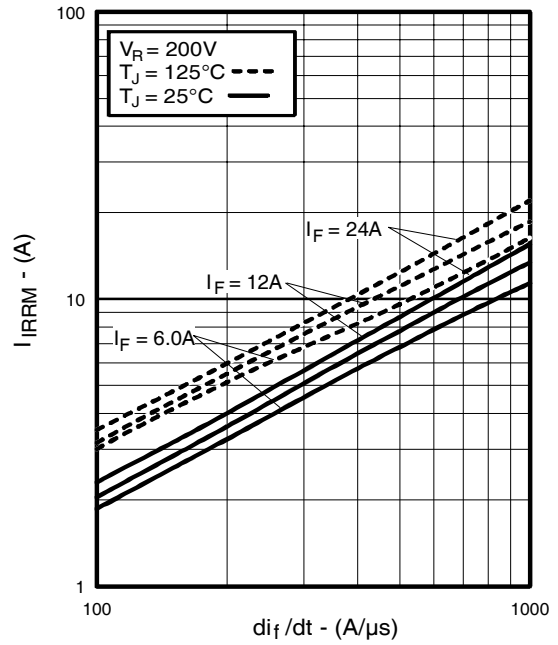


Fig. 15 - Typical Recovery Current vs. di_f/dt

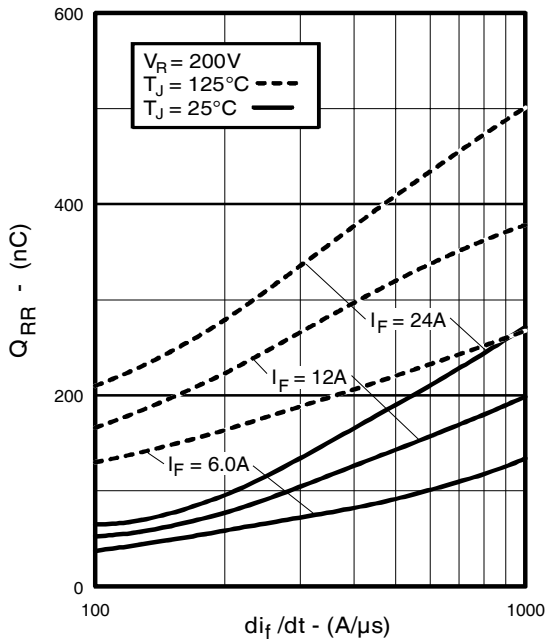


Fig. 16 - Typical Stored Charge vs. di_f/dt

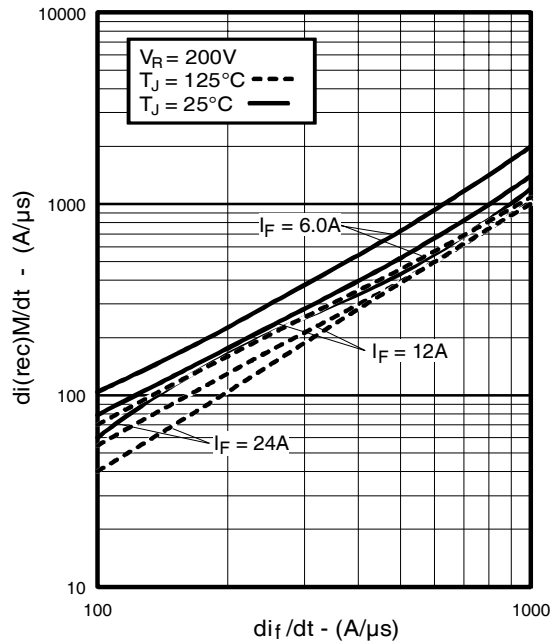


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

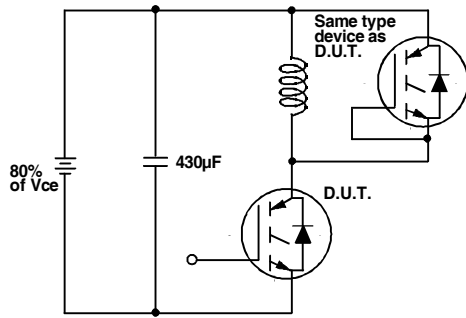


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

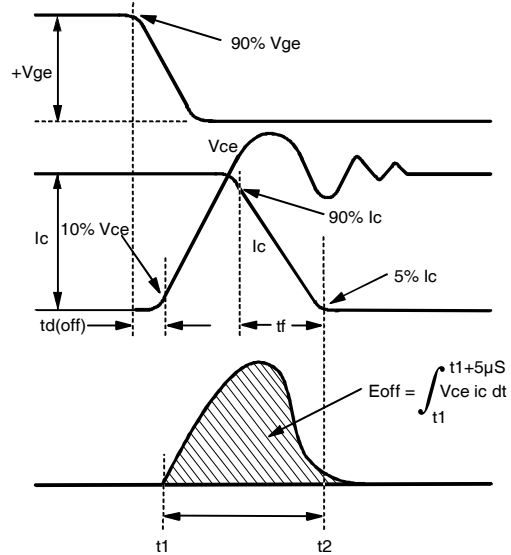


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

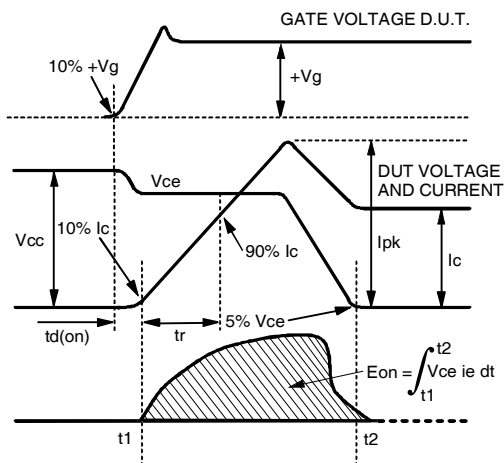


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

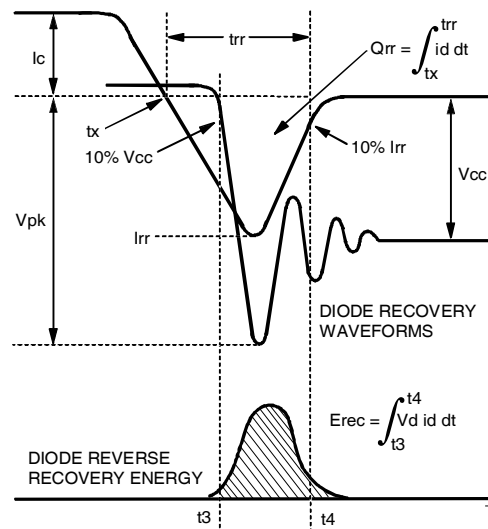


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

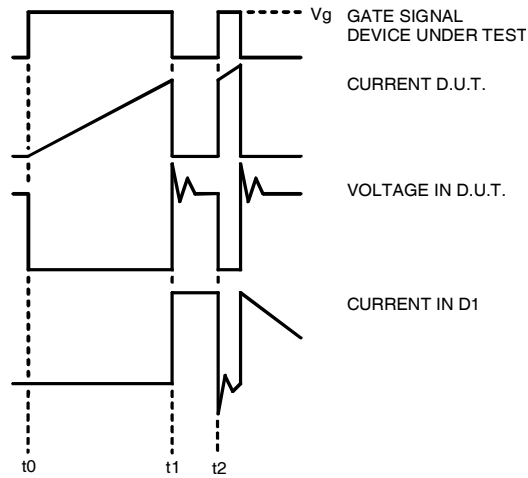


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

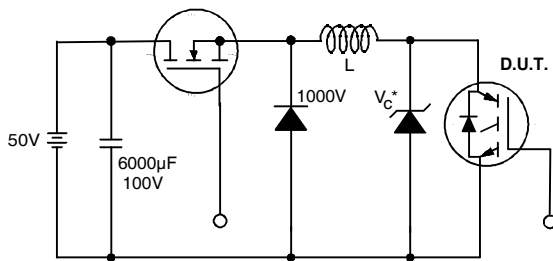
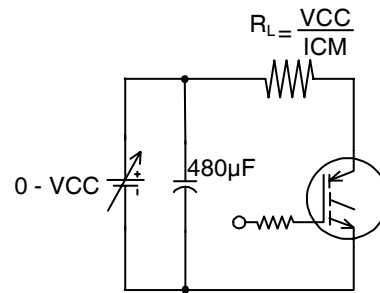


Figure 19. Clamped Inductive Load Test Circuit



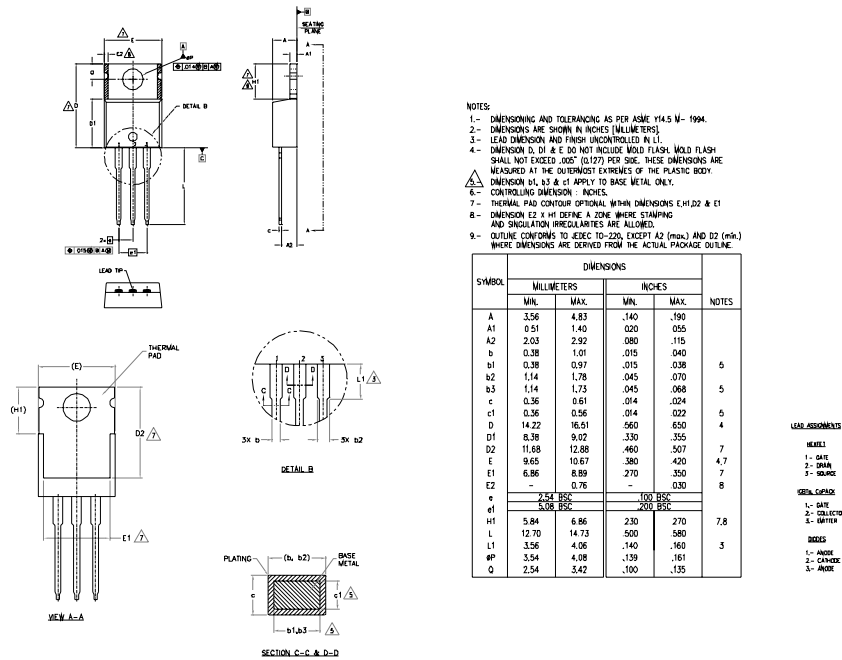
Pulsed Collector Current Test Circuit
 Figure 20. Pulsed Collector Current Test Circuit

IRG4BC30UDPbF

Notes:

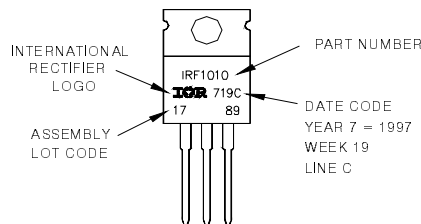
- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE 'C'
Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.